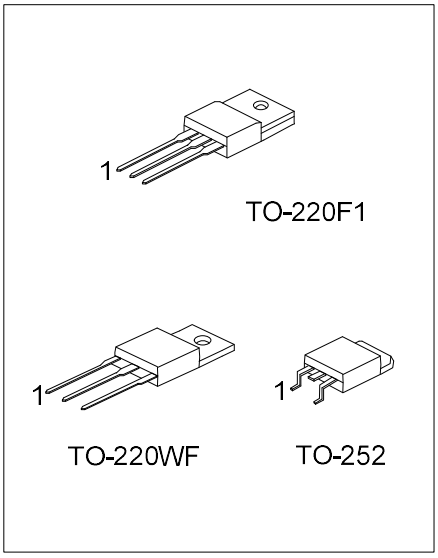
USJ60R380

Power MOSFET

13A, 600V N-CHANNEL SUPER-JUNCTION MOSFET



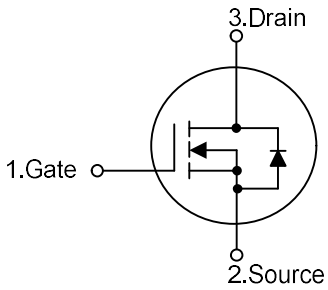
■ DESCRIPTION

The **UTC USJ60R380** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

■ FEATURES

* $R_{DS(ON)} \leq 0.38\ \Omega$ @ V_{GS} = 10V, I_D = 2.7A
* Fast switching capability
* Avalanche energy tested
* Improved dv/dt capability, high ruggedness
* Green Product

■ SYMBOL



■ ORDERING INFORMATION

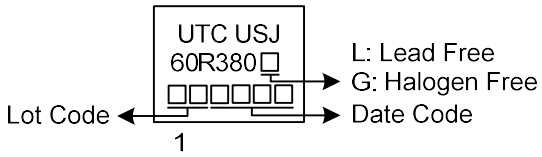
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
USJ60R380L-TF1-T	USJ60R380G-TF1-T	TO-220F1	G	D	S	Tube
-	USJ60R380G-TW1-T	TO-220WF	G	D	S	Tube
-	USJ60R380G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

USJ60R380G-TF1-T (1)Packing Type (2)Package Type (3)Green Package	(1) T: Tube, R: Tape Reel (2) TF1: TO-220F1, TW1: TO-220WF, TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free

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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	13	A
	Pulsed (Note 2)	I_{DM}	39	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	153	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	0.97	V/ns
Power Dissipation	TO-220F1/TO-220WF	P_D	29	W
	TO-252		59	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 100mH, I_{AS} = 1.8A, V_{DD} = 50V, R_G = 25 Ω Starting T_J = 25°C
4. I_{SD} ≤ 13A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F1/TO-220WF	$θ_{JA}$	62.5	°C/W
	TO-252		110	°C/W
Junction to Case	TO-220F1/TO-220WF	$θ_{JC}$	4.3	°C/W
	TO-252		2.1 (Note)	°C/W

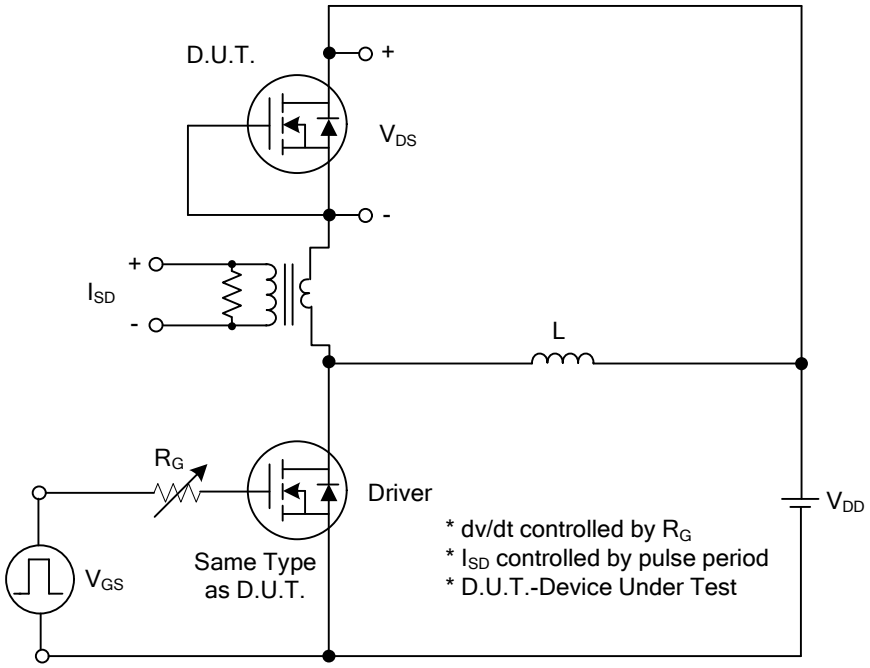
Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

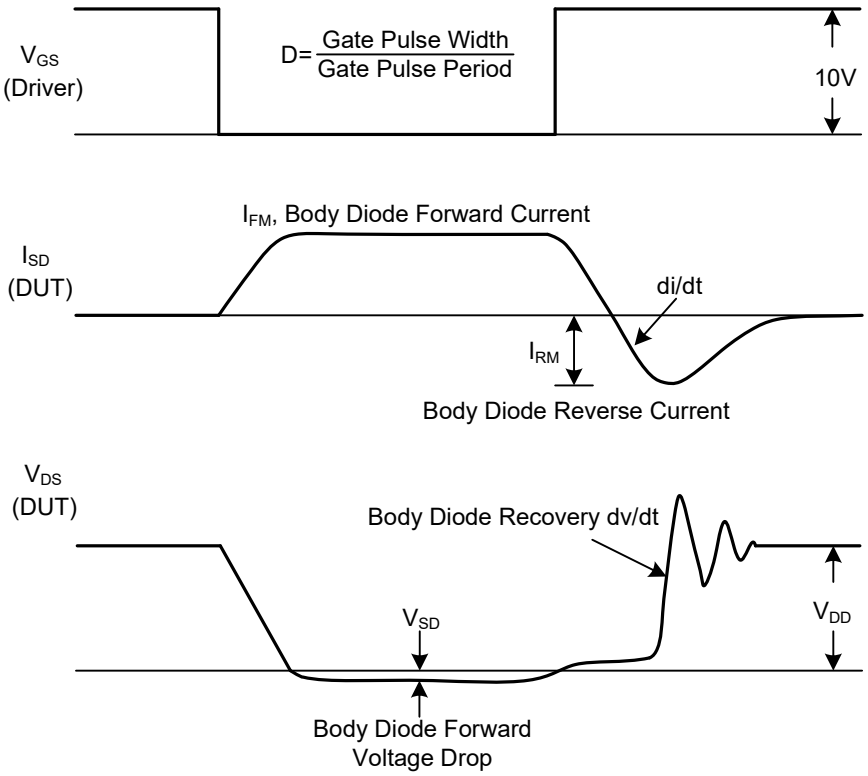
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=250μA	600			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=600V, V_{GS}=0V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{DS}=0V ,V_{GS}=25V			10	μA
	Reverse		V_{DS}=0V ,V_{GS}=-20V			-10	μA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.5		4.5	V
Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=2.7A			0.38	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=50V, f=1.0MHz		667		pF
Output Capacitance		C_{OSS}			182		pF
Reverse Transfer Capacitance		C_{RSS}			16		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q_G	V_{DS}=480V, V_{GS}=10V, I_D=13A (Note 1, 2)		31		nC
Gate to Source Charge		Q_{GS}			8		nC
Gate to Drain Charge		Q_{GD}			12		nC
Internal Gate Input Resistance		R_G	V_{GS}=0V, f=1MHz		2.48		Ω
Turn-ON Delay Time (Note 1)		$t_{D(ON)}$	V_{DD}=100V, V_{GS}=10V, I_D=13A, R_G=25Ω (Note 1, 2)		11		ns
Rise Time		t_R			26		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			85		ns
Fall-Time		t_F			35		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I_S				13	A
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	I_S=13A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t_{rr}	I_S =13A, V_{GS}=0V, dI_F/dt=100A/μs		308		ns
Body Diode Reverse Recovery Charge		Q_{rr}			3.7		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

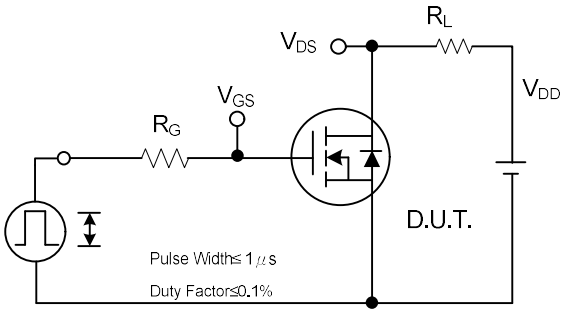


Peak Diode Recovery dv/dt Test Circuit

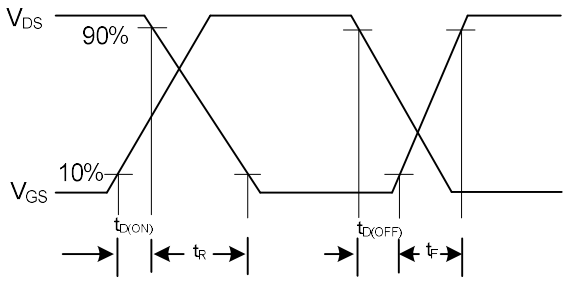


Peak Diode Recovery dv/dt Waveforms

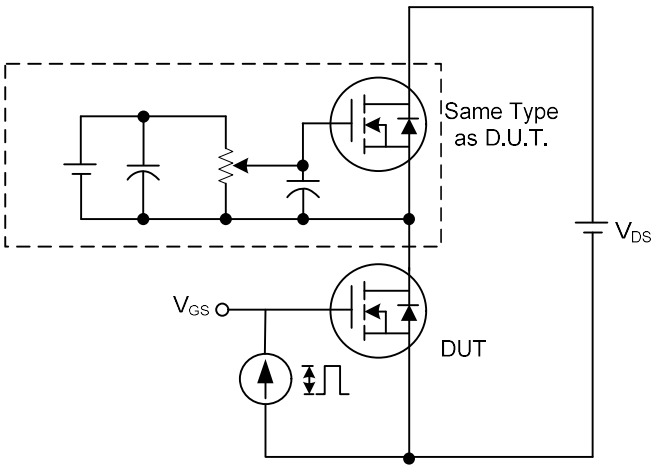
■ TEST CIRCUITS AND WAVEFORMS



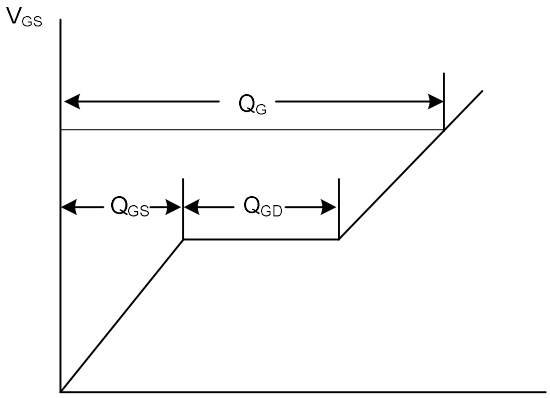
Switching Test Circuit



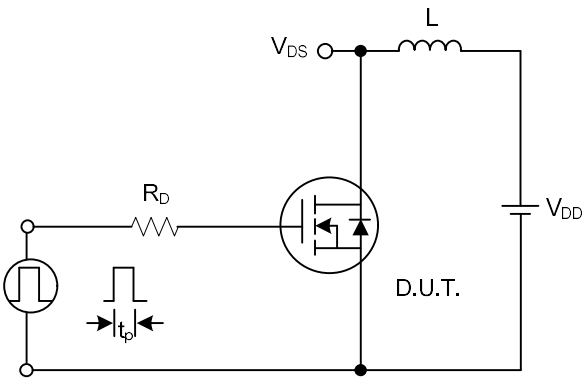
Switching Waveforms



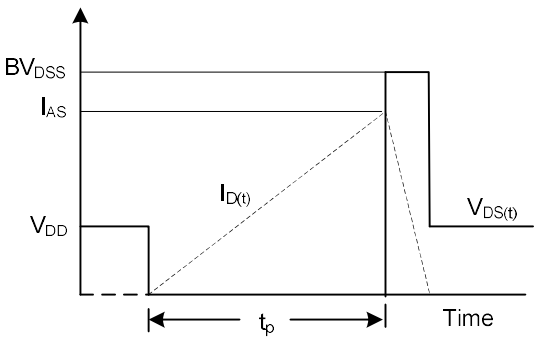
Gate Charge Test Circuit



Gate Charge Waveform



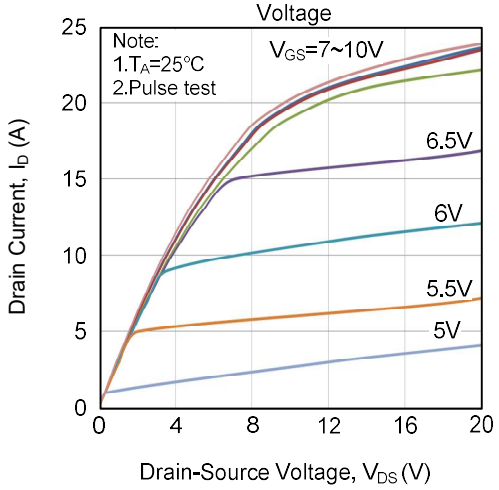
Unclamped Inductive Switching Test Circuit



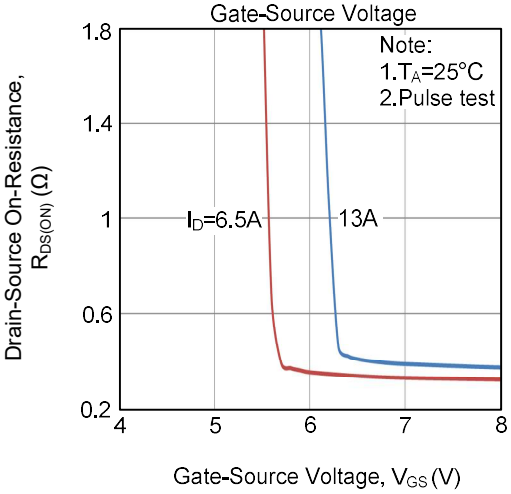
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

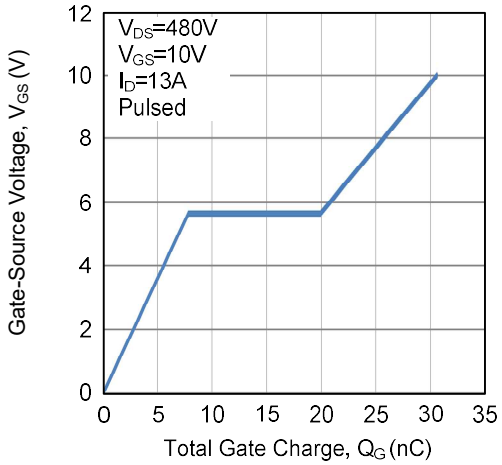
Drain Current vs. Drain-Source Voltage



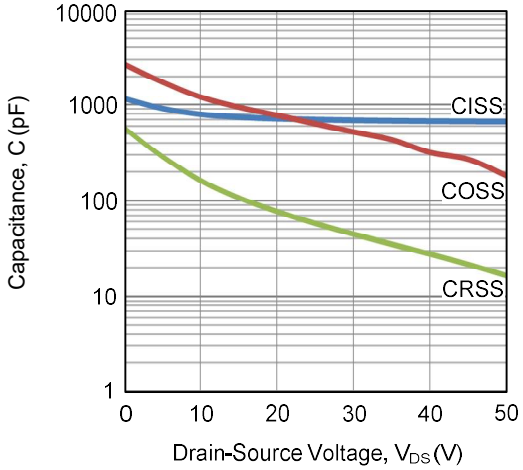
Drain-Source On-Resistance vs. Gate-Source Voltage



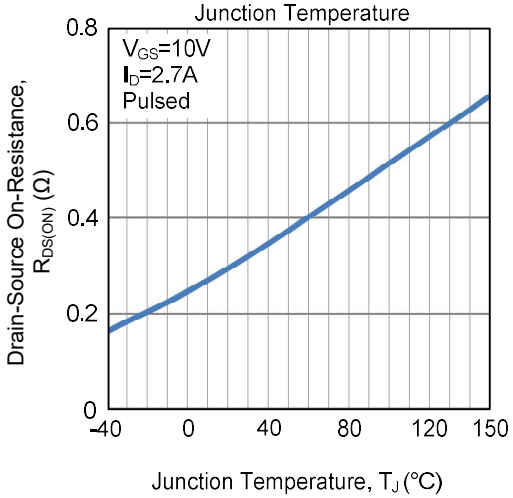
Gate Charge Characteristics



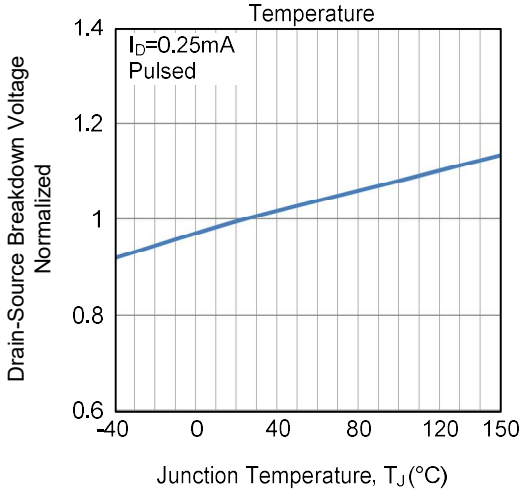
Capacitance Characteristics



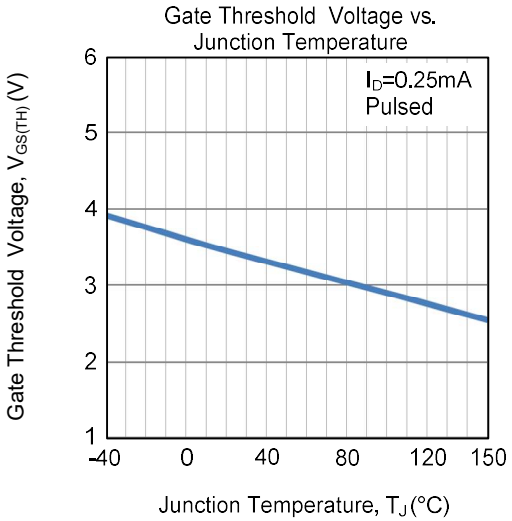
Drain-Source On-Resistance vs. Junction Temperature

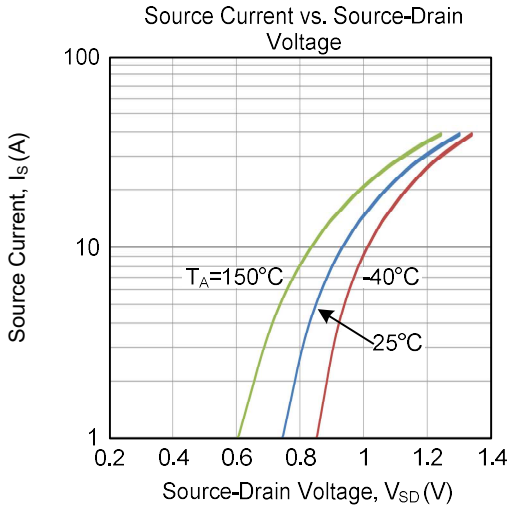


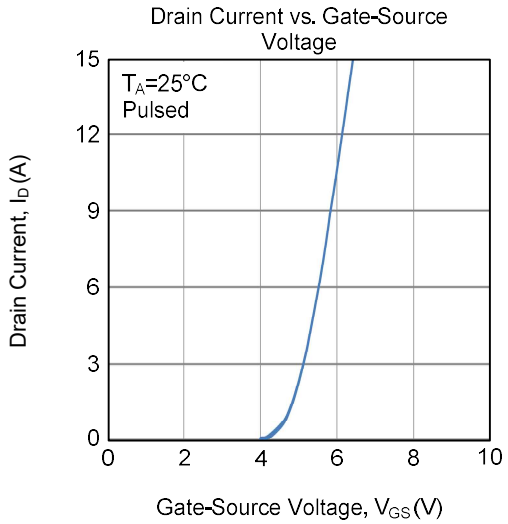
Breakdown Voltage vs. Junction Temperature

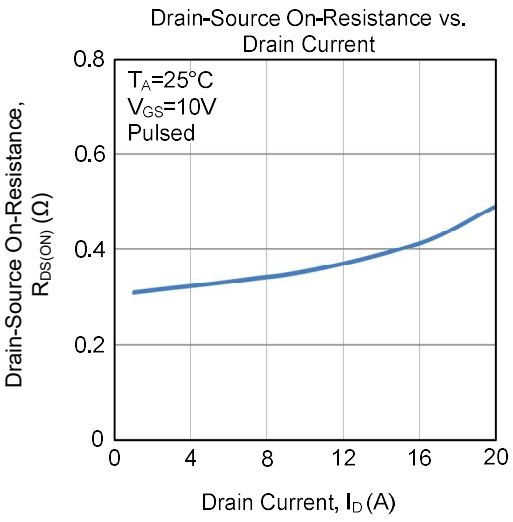


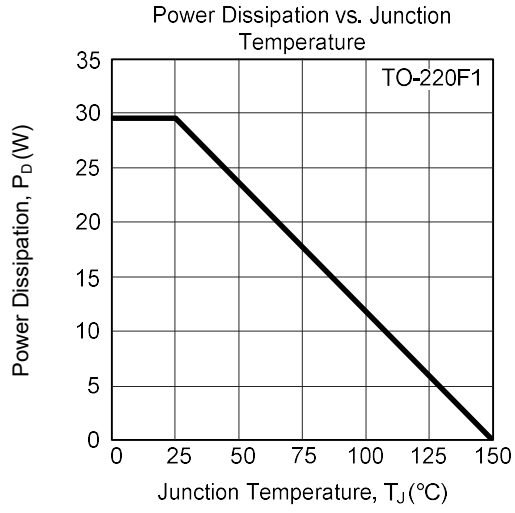
■ TYPICAL CHARACTERISTICS (Cont.)

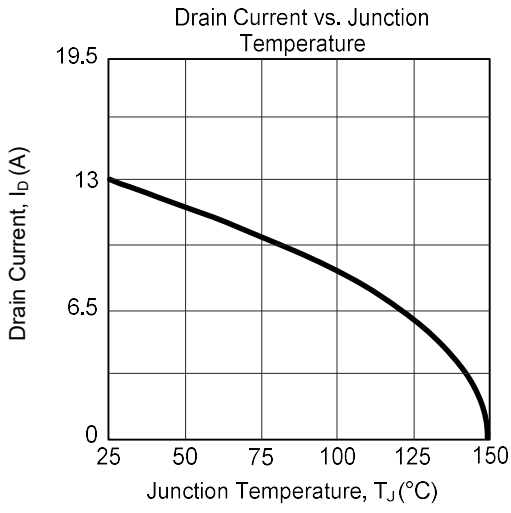




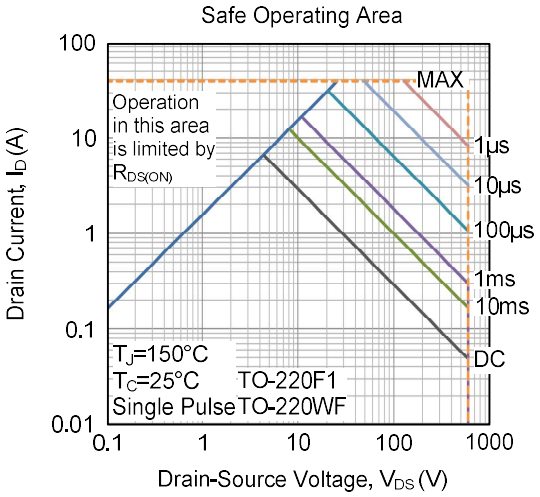


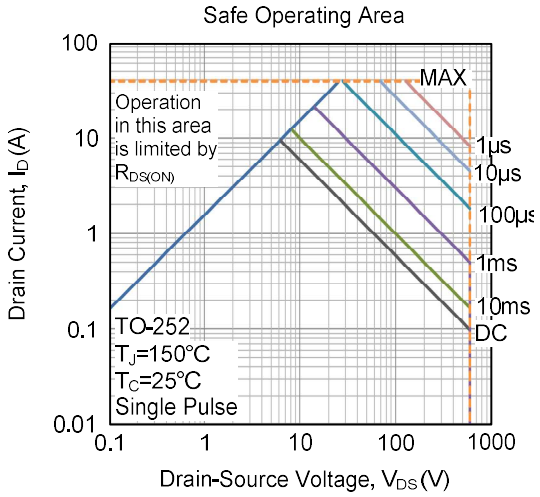






■ TYPICAL CHARACTERISTICS (Cont.)





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